General Description

The WST3400S is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST3400S meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

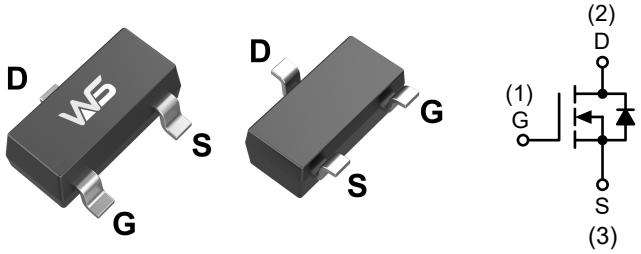
Product Summery

BV_{DSS}	R_{DSON}	I_D
30V	27mΩ	5.6A

Applications

- High Frequency Point-of-Load Synchronous s
  Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_c=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	5.6	A
I_D@T_c=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	4.2	A
I_{DM}	Pulsed Drain Current[2]	18	A
P_D@T_A=25℃	Total Power Dissipation[3]	1	W
P_D@T_A=70℃	Total Power Dissipation[3]	0.64	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	125	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	95	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	80	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.025	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=5A	---	27	32	mΩ
		V_{GS}=2.5V , I_D=4A	---	39	45	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.5	0.8	1.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.8	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=5A	---	7	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.5	5	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=5A	---	5.5	8.4	nC
Q_{gs}	Gate-Source Charge		---	2.1	3.5	
Q_{gd}	Gate-Drain Charge		---	1.5	2.9	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=5A	---	2.2	4.2	ns
T_r	Rise Time		---	6.8	9	
$T_{d(off)}$	Turn-Off Delay Time		---	3.5	5	
T_f	Fall Time		---	20	40	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	525	600	pF
C_{oss}	Output Capacitance		---	57	112	
C_{rss}	Reverse Transfer Capacitance		---	45	91	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	5.6	A
I_{SM}	Pulsed Source Current[2,4]		---	---	18	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.4	V
t_{rr}	Reverse Recovery Time	IF=5A , dI/dt=100A/μs , T_J=25℃	---	18	---	nS
Q_{rr}	Reverse Recovery Charge		---	1	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

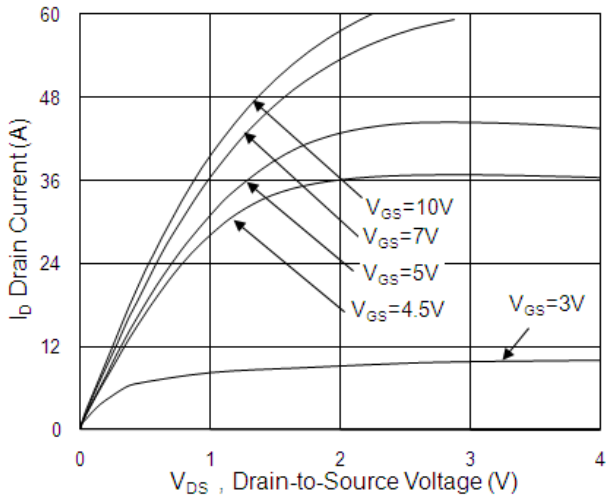


Fig.1 Typical Output Characteristics

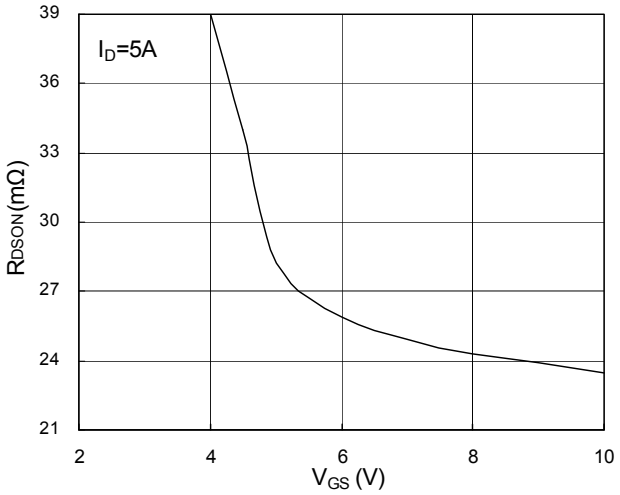


Fig.2 On-Resistance vs. Gate-Source

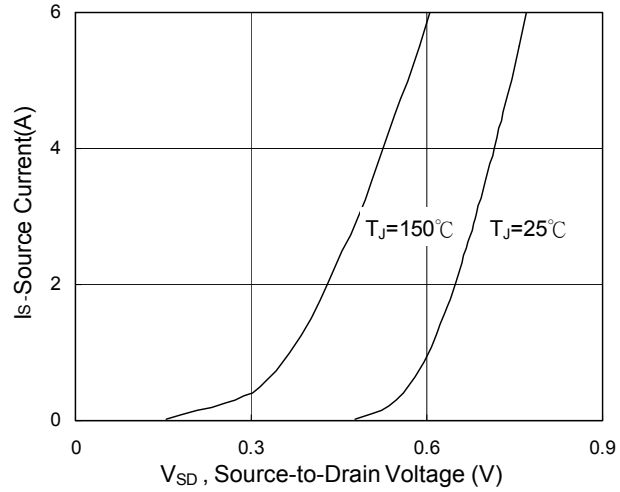


Fig.3 Forward Characteristics Of Reverse

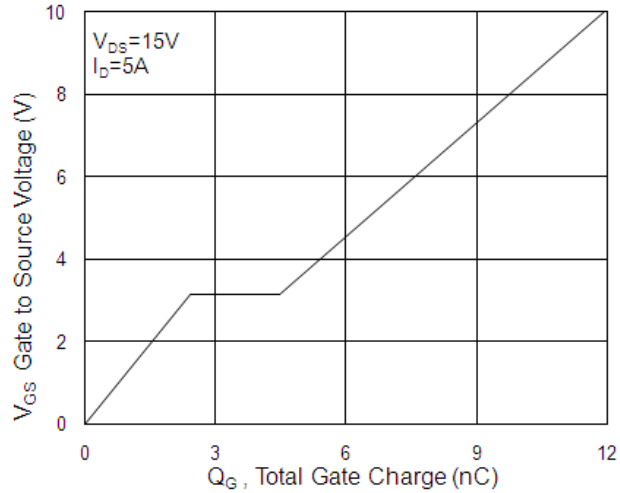


Fig.4 Gate-Charge Characteristics

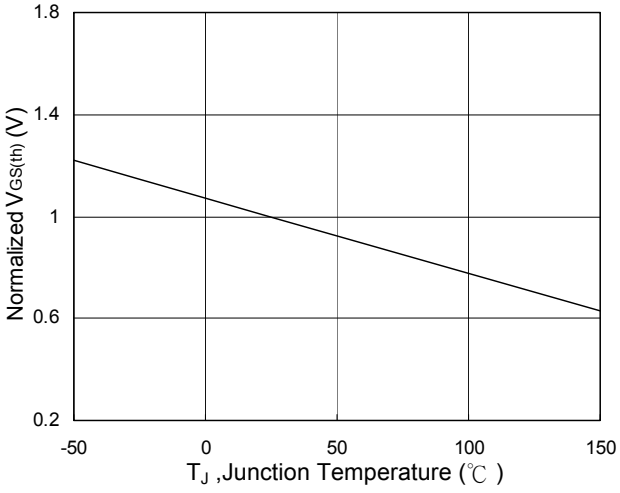


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

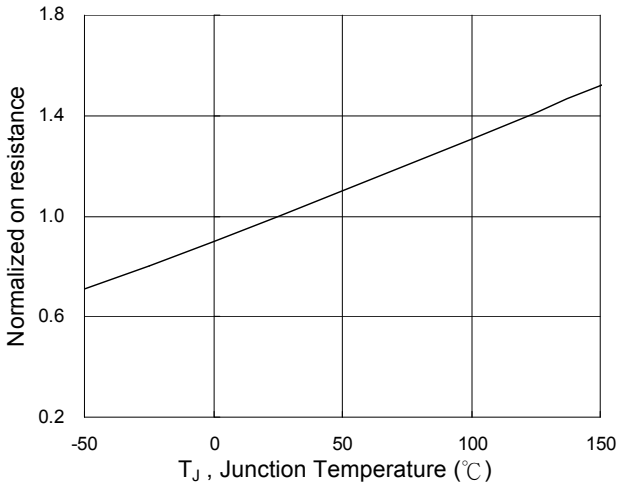


Fig.6 Normalized R_{DSON} vs. T_J

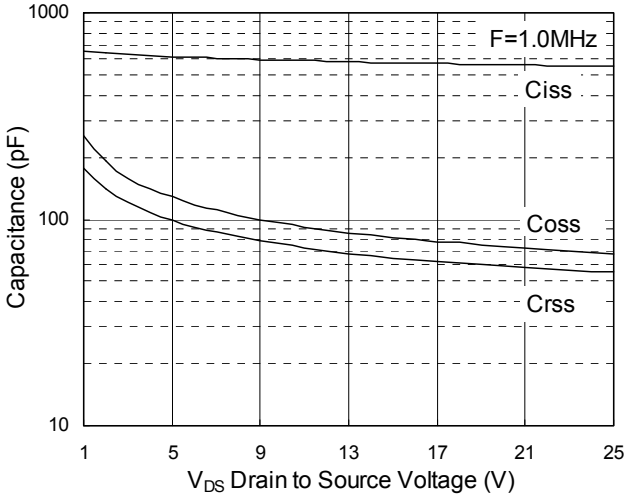


Fig.7 Capacitance

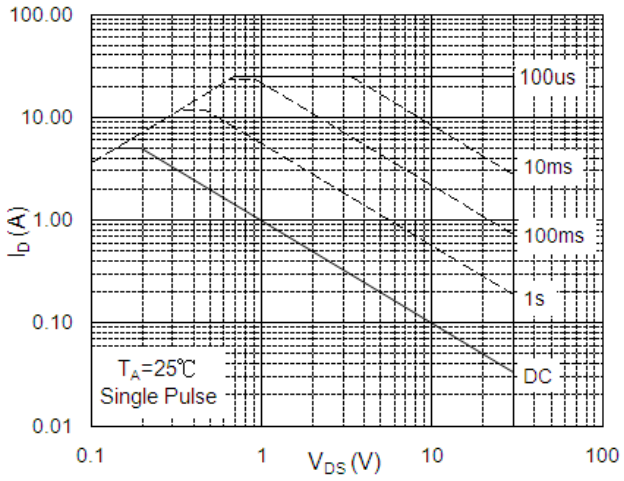


Fig.8 Safe Operating Area

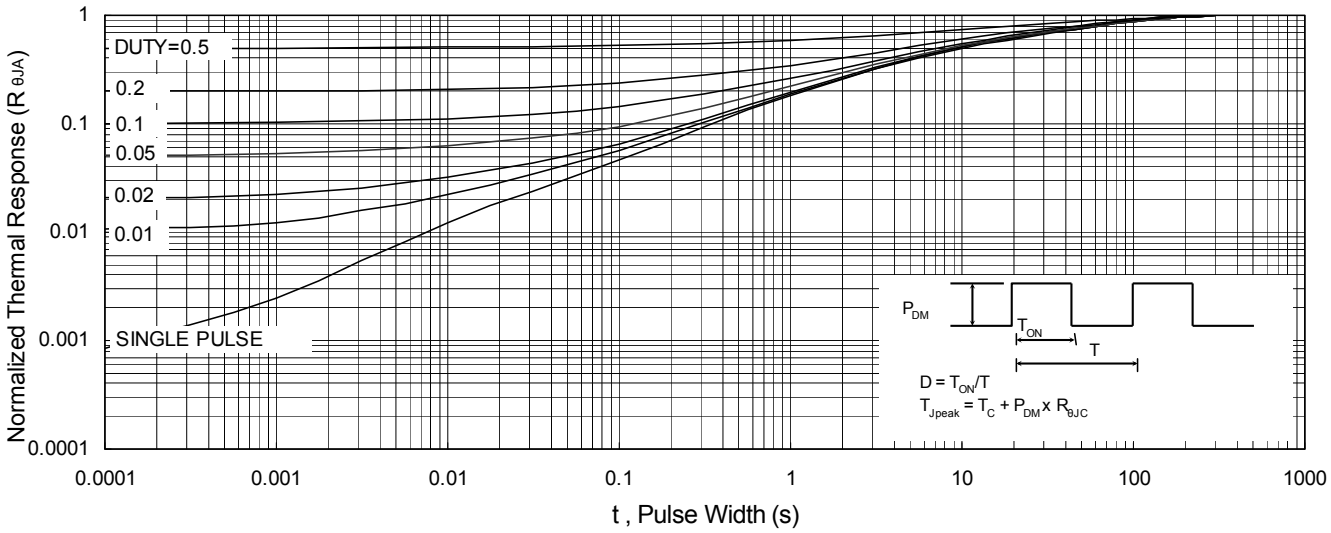


Fig.9 Normalized Maximum Transient Thermal Impedance

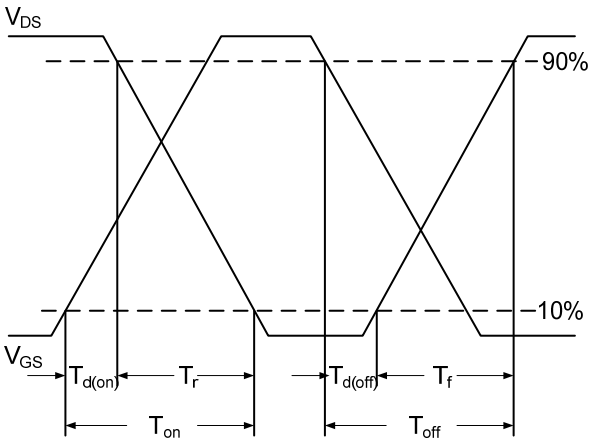


Fig.10 Switching Time Waveform

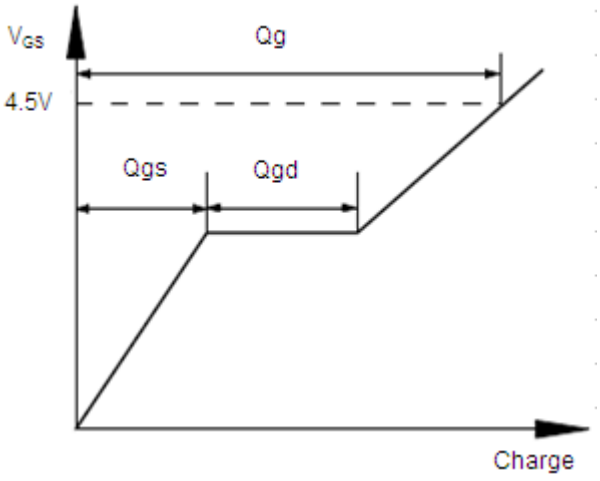
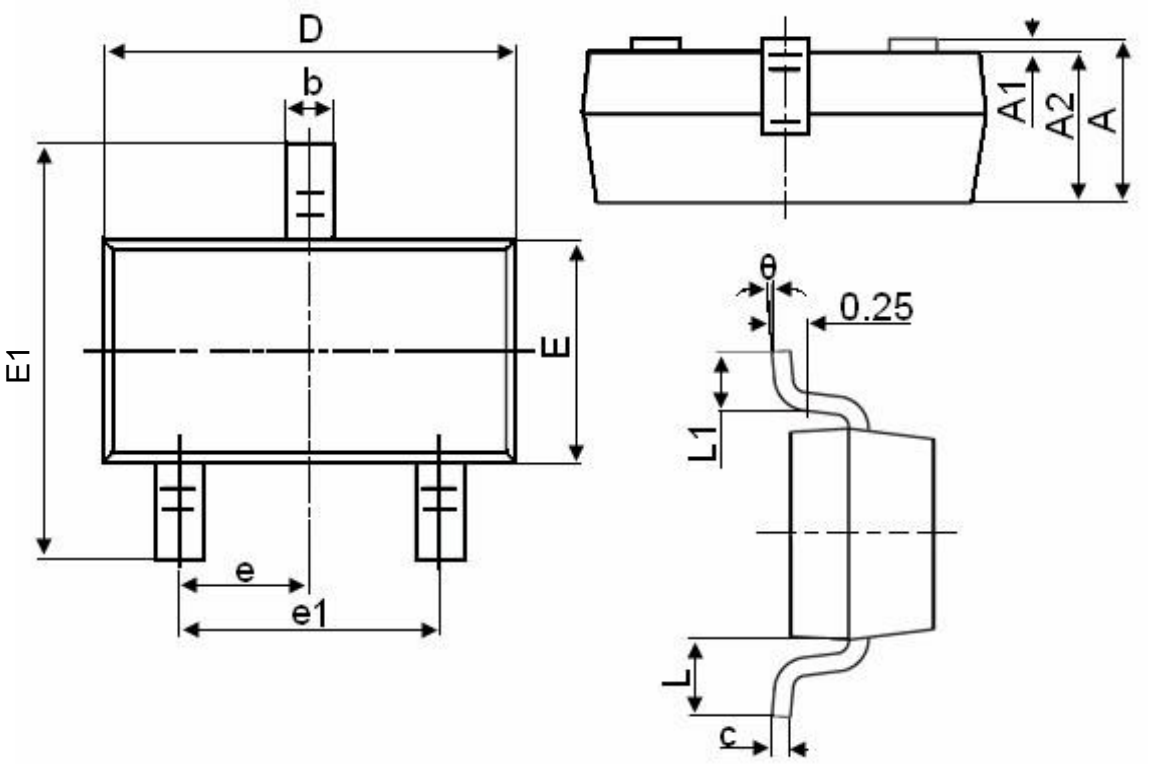


Fig.11 Gate Charge Waveform

Packaging information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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